



US 20230230901A1

(19) **United States**
(12) **Patent Application Publication** (10) **Pub. No.: US 2023/0230901 A1**
Farooq et al. (43) **Pub. Date: Jul. 20, 2023**

(54) **TSV AND BACKSIDE POWER DISTRIBUTION STRUCTURE**

(52) **U.S. Cl.**
CPC *H01L 23/481* (2013.01); *H01L 21/76898* (2013.01); *H01L 23/5286* (2013.01); *H01L 24/13* (2013.01); *H01L 24/16* (2013.01); *H01L 24/81* (2013.01); *H01L 25/105* (2013.01); *H01L 2224/13147* (2013.01); *H01L 2224/16225* (2013.01); *H01L 2224/81801* (2013.01)

(71) Applicant: **International Business Machines Corporation**, Armonk, NY (US)

(72) Inventors: **Mukta Ghate Farooq**, Hopewell Junction, NY (US); **Ruilong Xie**, Niskayuna, NY (US)

(21) Appl. No.: **17/572,101**

(22) Filed: **Jan. 10, 2022**

Publication Classification

(51) **Int. Cl.**
H01L 23/48 (2006.01)
H01L 23/528 (2006.01)
H01L 25/10 (2006.01)
H01L 23/00 (2006.01)
H01L 21/768 (2006.01)

(57) **ABSTRACT**

A semiconductor device includes an electronic circuit within a device layer; wherein the device layer is between a thin layer of wiring for signal connections having a first thickness and a thick layer of wiring for power having a second thickness, the second thickness being greater than the first thickness; a silicon layer above the device layer, the thin layer of wiring, and the thick layer of wiring; a first via connection from a top of the semiconductor device to the thin layer of wiring; a second via connection from the top of the semiconductor device to the thick layer of wiring; and a packaging substrate with a connection to the thick layer of wiring.

